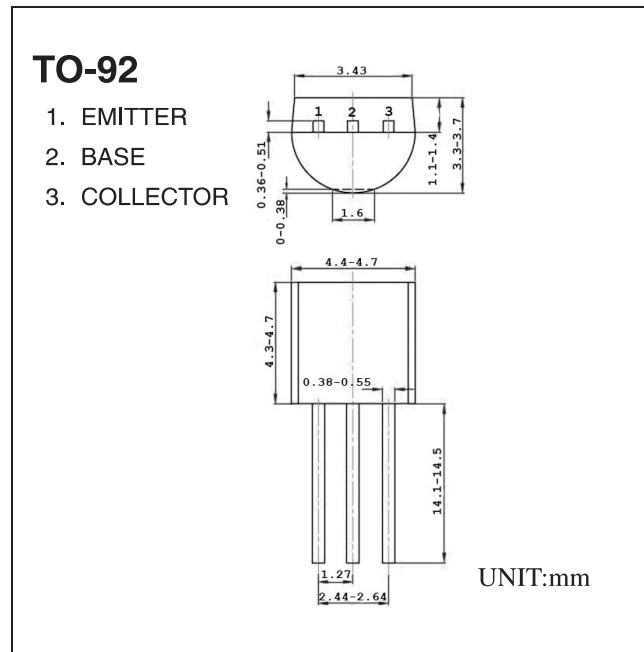


TRANSISTOR (PNP)

Plastic-Encapsulate Transistor

<p>FEATURES</p> <p>Power dissipation P_{CM}: 0.45W ($T_{amb}=25^{\circ}C$)</p> <p>Collector current I_{CM}: -0.1A</p> <p>Collector-base voltage $V_{(BR)CBO}$: -50V</p> <p>Operating and storage junction temperature range T_J, T_{stg}: $-55^{\circ}C$ to $+150^{\circ}C$</p>



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS
 Ratings at $25^{\circ}C$ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100 \mu A, I_E=0$	-50		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-45		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100 \mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$		-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-1mA$	60	1000	
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-100mA, I_B=-10mA$		-0.3	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-100mA, I_B=-10mA$		-1	V
Transition frequency	f_r	$V_{CE}=-5V, I_C=-10mA$ $f=30MHz$	150		MHz

CLASSIFICATION OF h_{FE}

Rank	A	B	C	D
Range	60-150	100-300	200-600	400-1000